

100V NPN LOW VCESAT TRANSISTOR IN PowerDI3333-8

Features

- BV_{CEO} > 100V
- Small Form Factor Thermally Efficient Package.
 Enables Higher Density End Products
- I_C = 5A High Continuous Collector Current
- I_{CM} = 10A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < 35mV
- hFE Specified Up to 10A for a High Gain Hold Up
- Complementary PNP Type: DXTP03100CFG
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

PowerDI3333-8 (SWP) (Type UX)

Mechanical Data

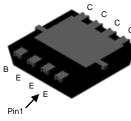
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic. "Green" Molding Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.03 grams (Approximate)

Applications

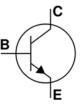
- Motor Driving
- Line Switching
- High Side Switches



Top View



Bottom View



Device Symbol

Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DXTN03100CFG-7	Standard	2J6	7	12	2,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

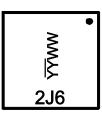
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

PowerDI3333-8 (SWP) (Type UX)



 $\frac{2J6}{YY} = \text{Product Type Marking Code}$ $\frac{Y}{YY} = \text{Date Code Marking}$ $\frac{YY}{Y} = \text{Last Two Digits of Year (ex: 21 = 2021)}$ WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated. DXTN03100CFG



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vсво	120	V
Collector-Emitter Voltage	Vceo	100	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	lc	5	A
Peak Pulse Current	Ісм	10	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Dever Dissinction	(Note 5)	D-	1.2	W
Power Dissipation	(Note 6)	PD PD	2.7	W
Thermal Desistance, Junction to Ambient	(Note 5)	D	107	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	- R _{0JA}	48	°C/W
Thermal Resistance, Junction to Leads (Note 7)		Rejl	8.5	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

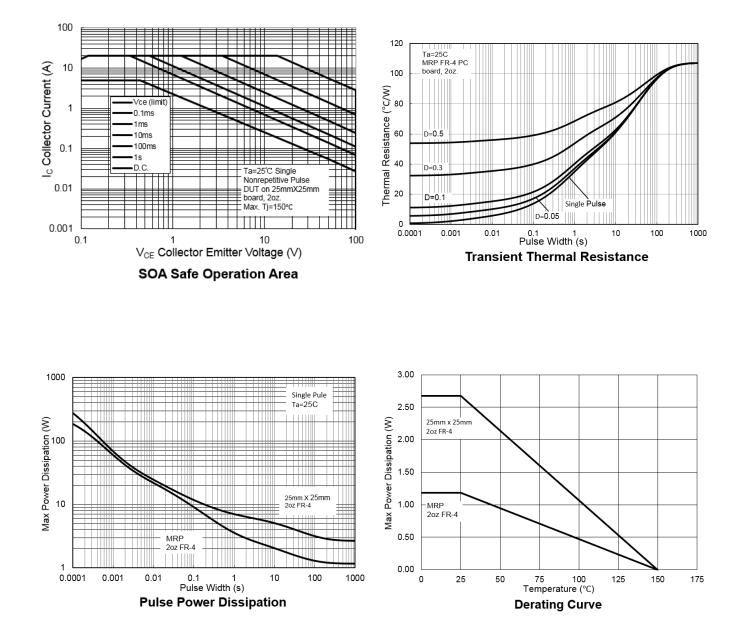
5. For a device mounted with the collector tab on MRP FR4-PCB; device is measured under still air conditions whilst operating in a steady-state. Notes: 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.

7. Thermal resistance from junction to solder-point (at the collector tab).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





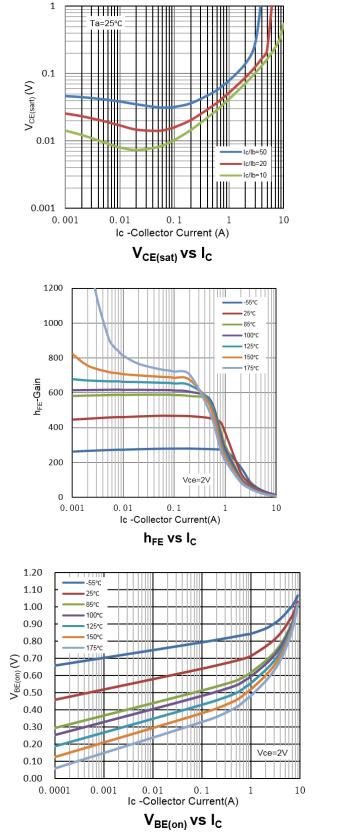
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

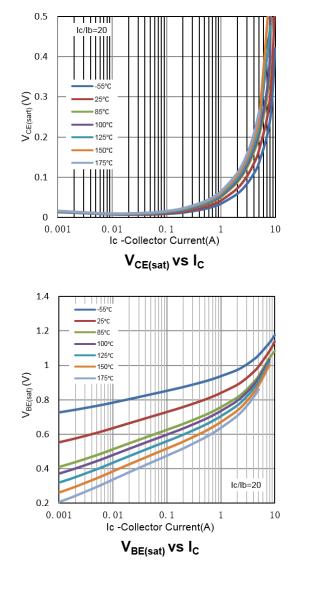
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	ВVсво	120	269		V	Ic = 100µA
Collector-Emitter Breakdown Voltage (Note 9)	BVCEO	100	121	_	V	Ic = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	7.9	_	V	I _E = 100μA
Collector-Base Cut-Off Current		—	2	20	nA	V _{CB} = 120V
Collector-Base Cut-Off Current	Ісво	_	0.07	10	μA	V _{CB} = 120V, T _A = +125°C
Callastar Fraittar Cut Off Current	ICER	_	2	20	nA	V _{CB} = 100V
Collector-Emitter Cut-Off Current	R ≤ 1kΩ	_	0.44	10	μA	V _{CB} = 100V, T _A = +125°C
Emitter Cut-Off Current	lebo	_	1	20	nA	V _{EB} = 6V
		200	459	_	_	Ic = 10mA, VcE = 2V
		200	465	800	_	Ic = 100mA, VcE = 2V
Statia Forward Current Transfer Datia (Nata 0)		200	372	—		$I_C = 1A, V_{CE} = 2V$
Static Forward Current Transfer Ratio (Note 9)	hfe	150	219	_	_	Ic = 1.5A, Vce = 2V
		100	142	_	_	$I_C = 2A, V_{CE} = 2V$
		—	39	_	_	$I_C = 5A, V_{CE} = 2V$
	VCE(sat)	_	17	35	mV	Ic = 100mA, I _B = 5mA
Collector Emitter Seturation Voltage (Note 0)		—	43	65	mV	Ic = 1A, I _B = 100mA
Collector-Emitter Saturation Voltage (Note 9)		—	88	125	mV	Ic = 2A, I _B = 100mA
		_	166	220	mV	$I_{C} = 5A, I_{B} = 500mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	—	992	1100	mV	$I_{C} = 5A, I_{B} = 500 \text{mA}$
Base-Emitter Turn-On Voltage (Note 9)	VBE(on)	—	894	1000	mV	$I_C = 5A, V_{CE} = 2V$
Input Capacitance	Cibo	—	550	_	pF	V _{EB} = 0.5V. f = 1MHz
Output Capacitance	C _{obo}	—	18	—	pF	V _{CB} = 10V. f = 1MHz
Transition Frequency	f⊤	_	140	—	MHz	$V_{CE} = 10V$, $I_C = 100mA$ f = 50MHz
	tdelay	—	16	_	ns	
Switching Time	trise	_	5	_	ns	Vcc = 10V, Ic = 1A
Switching Time	t _{storage}	_	1450	—	ns	$I_{B1} = -I_{B2} = 100 \text{mA}$
	t _{fall}	_	87	_	ns]

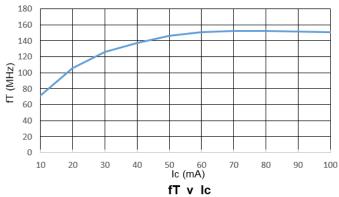
Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



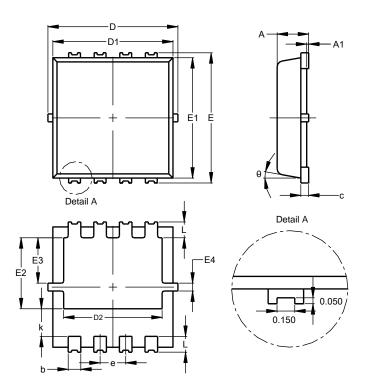






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



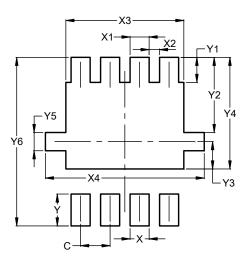
PowerDI3333-8	(SWP)	(Type U	X)

Pov	PowerDI3333-8 (SWP)						
(Type UX)							
Dim	Min	Max	Тур				
Α	0.75	0.85	0.80				
A1	0.00	0.05					
b	0.25	0.40	0.32				
С	0.10	0.25	0.15				
D	3.20	3.40	3.30				
D1	2.95	3.15	3.05				
D2	2.30	2.70	2.50				
Е	3.20	3.40	3.30				
E1	2.95	3.15	3.05				
E2	1.60	2.00	1.80				
E3	0.95	1.35	1.15				
E4	0.10	0.30	0.20				
е	_	_	0.65				
k	0.50	0.90	0.70				
L	0.30	0.50	0.40				
θ	0°	12°	10°				
All I	Dimens	sions ir	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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